

# FOR USE BY ELECTRICIANS OVERSEAS :

**最新トランジスタ規格表** (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 ( $T_c=25^\circ\text{C}$ )					電気的特性 ( $T_c=25^\circ\text{C}$ )										外形	備考	
				$V_{ce0}$ (V)	$V_{be0}$ (V)	$I_c$ (mA)	$P_c$ (mW)	$T_c$ ( $^\circ\text{C}$ )	$I_{c0}$ 最大値 ( $\mu\text{A}$ )	直流又はパルス $h_{FE}$		バイアス		$h_{FE}$	$h_{ie}$	$h_{re}$	$h_{oe}$	$f_{\alpha}$			$C_{ob}$
1	2	3	4	5					6		7		8				9	10		11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6  $I_{CBO}$  MAXIMUM VALUE AND  $V_{CB}$  VALUE (CRITERIA FOR MEASURING  $I_{CBO}$ )
- 7 STANDARD VALUE OF DC/PULSE  $h_{FE}$  AND  $V_{CE}$ ,  $I_C$  (CRITERIA FOR MEASURING DC/PULSE  $h_{FE}$ )
- 8 STANDARD VALUE OF  $h$  PARAMETERS AND BIAS  $V_{CB}$ ,  $I_E$  (CRITERIA FOR MEASURING  $h$  PARAMETERS)

- \* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9  $f_{\alpha b}$  OF RF CHARACTERISTIC, EXCEPT IN CASE OF \* WHICH INDICATES VALUE OF  $f_T$ .
- 10  $C_{ob}$  AND  $r_{bb'}$  OF RF CHARACTERISTICS EXCEPT IN CASE OF \* IN  $r_{bb'}$  COLUMN WHICH INDICATES VALUE OF  $h_{ie}$  (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO .....

型名	社名	用途	構造	最大定格 (T <sub>a</sub> = 25°C)					電 気 的 特 性 (T <sub>a</sub> = 25°C)										外形	備考				
				V <sub>CB0</sub> (V)	V <sub>EBO</sub> (V)	I <sub>C</sub> (mA)	P <sub>C</sub> (mW)	T <sub>J</sub> (°C)	I <sub>CB0</sub> 最大値 (μA)	V <sub>CB</sub> (V)	直流又はパルス h <sub>FE</sub>		バイアス		h <sub>fe</sub> h <sub>fe</sub> *	h <sub>ie</sub> h <sub>ie</sub> * (Ω)	h <sub>re</sub> h <sub>re</sub> * (×10 <sup>-4</sup> )	h <sub>oe</sub> h <sub>oe</sub> * (μU)			f <sub>β</sub> f <sub>T</sub> * (MHz)	C <sub>ob</sub> (pF)	r <sub>bb</sub> h <sub>ie</sub> (real) (Ω)*	
											V <sub>CE</sub> (V)	I <sub>C</sub> (mA)	V <sub>CB</sub> (V)	I <sub>E</sub> (mA)										
2SC945	日電	RF. AF	Si. E	60	5	100	250	125	0.1	60	200	6	1	6	-10					250*	3	25*	138	2SA733 とコンプリ
" 946																								
" 947	松下	RF. Conv. Mix. Osc. PA	Si. P	25	3	15	150	175	100	25	20	10	2	10	-3					650*	C <sub>re</sub> 0.33pS	20	50C	
" 948	"	RF	"	25	3	15	150	175	100	25	24	10	3	10	-3					800*	C <sub>re</sub> 0.33pS	30	50C	
" 949	新日無	RF. AF. LN	Si. EP	45	5	50	200	125	0.05	20	150	6	1	6	-0.3	200	12k	1.4	4.3	200*	2	C <sub>e</sub> r <sub>bb</sub> 60pS	138	2SA763 とコンプリ
" 950	"	RF. AF	"	30	5	100	300	125	0.1	20	100	6	1	10	-2					100*	4	C <sub>e</sub> r <sub>bb</sub> 75pS	138	2SA572 とコンプリ
" 951	"	"	"	60	5	100	300	125	0.1	20	100	6	1	10	-2					100*	4	C <sub>e</sub> r <sub>bb</sub> 75pS	138	2SA574 とコンプリ
" 952	"	RF	"	100	5	100	300	125	0.1	70	100	6	1	10	-2					100*	4	C <sub>e</sub> r <sub>bb</sub> 75pS	138	2SA575 とコンプリ
" 953	"	"	"	30		200	600	125	0.5	20	80	1	100	10	-5					90*	5	C <sub>e</sub> r <sub>bb</sub> 50pS	31	
" 954	"	RF. PA	"	60		400	600	125	0.5	20	100	1	100	10	-5					90*	5	C <sub>e</sub> r <sub>bb</sub> 50pS	31	
" 955	"	RF	"	20		50	150	125	1	10	100	6	1	6	-2					150*	2	C <sub>e</sub> r <sub>bb</sub> 250pS	29	
" 956	"	RF. AF	"	50	5	50	150	125	0.1	20	250	6	1	6	-1					200*	2	C <sub>e</sub> r <sub>bb</sub> 200pS	29	
* " 957	ソニー	RF	Si. DB	30		100	360	100	0.3	15	30	3	1	10	-10						1.5	C <sub>e</sub> r <sub>bb</sub> 10pS	206C	
" 958																								
* " 959	日電	PA	Si. E	120	5	700	700	150	3	80	80	5	200	10	-100					>50*	<50	35*	84B	2SA606 とコンプリ
* " 960	"	"	"	120	5	700	1W	150	3	80	80	5	200	10	-100					>50*	<50	35*	97B	2SA607 とコンプリ
* " 961	芝電	PA	Si. TMe	120	5	7A	60W (T <sub>c</sub> =25°C)	150	100	30	60	4	1A	5	-500					13*	350	5	102	
" 962	"	"	"	100	5	7A	60W (T <sub>c</sub> =25°C)	150	100	30	60	4	1A	5	-500								102	
* " 963	富士通	RF	Si. EP	35	4	50	250	175	2	12	70	6	1	6	-1	100				200*	2	50*	55C	
* " 964	"	"	"	35	4	50	250	175	2	12	100	6	1	6	-1		4000	5	20	200*	2	50*	55C	
* " 965	"	RF. SW	"	45	4	100	250	175	0.5	12	130	6	1	6	-1	t <sub>r</sub> < 80nS, t <sub>f</sub> < 100nS t <sub>avg</sub> < 200nS				200*	2	50*	55C	
* " 966	"	RF. AF. LN	"	30	5	200	500	175	0.5	12	160	4	10	6	-1	120	3500	0.1	5	70*	10	80	55C	
* " 967	"	RF. AF. PA	"	30	5	500	500	175	1	12	160	4	10	6	-1	120	3500	0.1	5	70*	10	70	55C	
* " 968	"	RF. PA	"	50	5	500	500	175	1	12	160	4	10	6	-1					70*	10	40	55C	
* " 969	"	RF. AF. LN	"	50		200	500	175	0.1	12	160	4	10	6	-1		3500	0.1	5	60*	10	80	55C	
* " 970	"	RF. SW	"	50	7	500	500	175	0.5	12	160	4	10	6	-1	t <sub>r</sub> < 80nS, t <sub>f</sub> < 150nS t <sub>avg</sub> < 800nS				70*	10	70	55C	
* " 971	"	RF. PA	"	50	5	500	1W	175	1	12	160	4	10	6	-1					70*	10	40	90	
* " 972	三洋	"	"	70	5	400	600	150	10	70	40-200	4	200	4	-10					80*				
* " 973	三菱	PA	"	40	4	500	7W (T <sub>c</sub> =25°C)	175	50	15	50	10	100							P <sub>o</sub> = 4W (f = 500MHz, V <sub>cc</sub> = 13.5V, P <sub>i</sub> = 1W)			126	
* " 974	"	"	"	35		1A	10W (T <sub>c</sub> =25°C)	200	100	15	50	10	100							P <sub>o</sub> = 6W (f = 500MHz, V <sub>cc</sub> = 13.5V, P <sub>i</sub> = 2W)			126	